

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO				<i>Complete If Known</i>	
				Based On	
				Filing Date	June 27, 2003
				First Named Inventor	Akihisa SHIMOMURA et al.
				Group Art Unit	
				Examiner Name	
Sheet	1	of	2	Attorney Docket Number	0756-7171

U.S. PATENT DOCUMENTS						
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>3</sup> (if known)			
SDI		6,165,876		Yamazaki et al.	12/26/2000	
		4,199,773		Goodman et al.	04/22/1980	
		4,463,492		Maeguchi	08/07/1984	
		4,775,641		Duffy et al.	10/04/1988	
		5,403,762		Takemura	04/04/1995	
		5,064,775		Chang	11/12/1991	
		4,168,990		Lenie et al.	09/25/1979	
		5,532,175		Racanelli et al.	07/02/1996	
		5,565,690		Theodore et al.	10/15/1996	
		4,169,740		Kalbitzer et al.	10/02/1979	
		5,501,989		Takayama et al.	03/26/1996	
		5,244,820		Kamata et al.	09/14/1993	
		2002/0006705	A1	Suzawa et al.	01/17/2002	
		2002/0014625	A1	Asami et al.	02/07/2002	
		2002/0048864	A1	Yamazaki et al.	04/25/2002	
		2002/0098628	A1	Hamada et al.	07/25/2002	
		2002/0004292	A1	Yamazaki et al.	01/10/2002	

FOREIGN PATENT DOCUMENTS							
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>2</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>3</sup> (if known)			
SDI		JP	2001-144027		05/25/2001		Abst.
		JP	2002-124685		04/26/2002		Abst.
		JP	2002-083805		03/22/2002		Abst.
		JP	2002-324808		11/08/2002		U.S. equiv.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS							
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					T <sup>2</sup>
SDI	✓	Y. Mishima et al., "Implantation Temperature Effect on Polycrystalline Silicon by Ion Shower Doping," Journal of Applied Physics, Vol. 74, Dec. 15, 1993, No. 12, pp. 7114-7117					X

Examiner Signature	<i>Stanetta Isaac</i>	Date Considered	3/17/05
--------------------	-----------------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Please type a plus sign (+) inside this box → [+]

PTO/SB/08A (08-00)

Approved for use through 10/31/2002. OMB 0651-0031

Approved for use August 18, 2001. GPO 2001-085  
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

**Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.**

<p><b>Substitute for form 1449A/PTO</b></p> <p><b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b></p> <p><i>(use as many sheets as necessary)</i></p>				<b><i>Complete if Known</i></b>
Based On				
Filing Date				June 27, 2003
First Named Inventor				Akihisa SHIMOMURA et al.
Group Art Unit				
Examiner Name				
Sheet	2	of	2	Attorney Docket Number
				0756-7171

U.S. PATENT DOCUMENTS

## **FOREIGN PATENT DOCUMENTS**

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SDI	<input checked="" type="checkbox"/>	Laviron et al., "Excimer-Laser Activation of Dopants in Silicon: A New Concept for a Uniform Treatment Over a Whole Die Area," International Workshop on Junction Technology, 2001, pp. 6-1-1 ~ 6-1-4	<input checked="" type="checkbox"/>
SDI	<input checked="" type="checkbox"/>	Specification, drawings and pending claims of U.S. Application Serial No. 09/255,777 filed February 23, 1999, entitled SEMICONDUCTOR DEVICE AND METHOD FOR FORMING THE SAME	<input checked="" type="checkbox"/>
SDI	<input checked="" type="checkbox"/>	Sasaki et al., "12.3: High Throughput CW-Laser Lateral Crystallization for Low-Temperature Poly-Si TFTs and Fabrication of 16 bit SRAMs and 270MHz Shift Registers," SID 02 DIGEST, pp. 154-157	<input checked="" type="checkbox"/>

**Examiner  
Signature**

Stanetta Basa

**Date Considered**

3/17/05

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.